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SiGe HBT GAIN BLOCK MMIC AMPLIFIER, DC - 5 GHz

Typical Applications

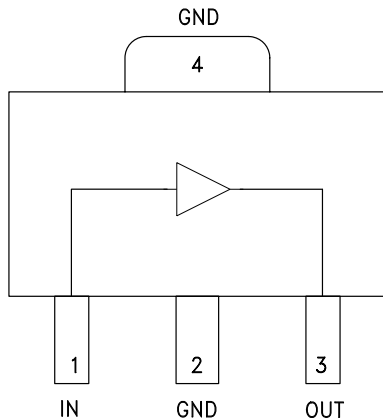
The HMC481ST89 / HMC481ST89E is an ideal RF/IF gain block & LO or PA driver for:

- Cellular / PCS / 3G
- Fixed Wireless & WLAN
- CATV, Cable Modem & DBS
- Microwave Radio & Test Equipment

Features

- P1dB Output Power: +19 dBm
- Gain: 20 dB
- Output IP3: +33 dBm
- Cascadable 50 Ohm I/Os
- Single Supply: +6V to +12V
- Industry Standard SOT89 Package
- Included in the HMC-DK001 Designer's Kits

Functional Diagram



General Description

The HMC481ST89 & HMC481ST89E are SiGe Heterojunction Bipolar Transistor (HBT) Gain Block MMIC SMT amplifiers covering DC to 5 GHz. Packaged in an industry standard SOT89, the amplifier can be used as a cascadable 50 Ohm RF/IF gain stage as well as a LO or PA driver with up to +21 dBm output power. The HMC481ST89(E) offer 20 dB of gain with a +33 dBm output IP3 at 1 GHz while requiring only 79 mA from a single positive supply. The Darlington feedback pair used results in reduced sensitivity to normal process variations and excellent gain stability over temperature while requiring a minimal number of external bias components.

Electrical Specifications, $V_s = 8.0\text{ V}$, $R_{bias} = 39\text{ Ohm}$, $T_A = +25^\circ\text{ C}$

| Parameter | Min. | Typ. | Max. | Units | |
|---|---------------|------|-------|-------|--------|
| Gain | DC - 1.0 GHz | 18 | 20 | dB | |
| | 1.0 - 2.0 GHz | 15.5 | 17.5 | dB | |
| | 2.0 - 3.0 GHz | 13 | 15 | dB | |
| | 3.0 - 4.0 GHz | 11 | 13 | dB | |
| | 4.0 - 5.0 GHz | 9 | 11 | dB | |
| Gain Variation Over Temperature | DC - 5 GHz | | 0.008 | 0.016 | dB/ °C |
| Input Return Loss | DC - 1.0 GHz | | 12 | | dB |
| | 1.0 - 5.0 GHz | | 15 | | dB |
| Output Return Loss | DC - 1.0 GHz | | 17 | | dB |
| | 1.0 - 4.0 GHz | | 27 | | dB |
| | 4.0 - 5.0 GHz | | 23 | | dB |
| Reverse Isolation | DC - 5 GHz | | 18 | | dB |
| Output Power for 1 dB Compression (P1dB) | 0.5 - 1.0 GHz | 16 | 19 | | dBm |
| | 1.0 - 2.0 GHz | 15 | 18 | | dBm |
| | 2.0 - 3.0 GHz | 13 | 16 | | dBm |
| | 3.0 - 4.0 GHz | 11 | 14 | | dBm |
| | 4.0 - 5.0 GHz | 9 | 12 | | dBm |
| Output Third Order Intercept (IP3) (Pout= 0 dBm per tone, 1 MHz spacing) | 0.5 - 2.0 GHz | | 33 | | dBm |
| | 2.0 - 3.0 GHz | | 30 | | dBm |
| | 3.0 - 4.0 GHz | | 27 | | dBm |
| | 4.0 - 5.0 GHz | | 25 | | dBm |
| Noise Figure | DC - 4 GHz | | 3.5 | | dB |
| | 4.0 - 5.0 GHz | | 4.0 | | dB |
| Supply Current (Icq) | | | 79 | | mA |

Note: Data taken with broadband bias tee on device output.

HMC481ST89* PRODUCT PAGE QUICK LINKS

Last Content Update: 02/23/2017

COMPARABLE PARTS

View a parametric search of comparable parts.

EVALUATION KITS

- HMC481ST89 Evaluation Board

DOCUMENTATION

Data Sheet

- HMC481ST89: SiGe HBT Gain Block MMIC Amplifier, DC - 5 GHz Data Sheet

TOOLS AND SIMULATIONS

- HMC481ST89 S-Parameters

REFERENCE MATERIALS

Quality Documentation

- Package/Assembly Qualification Test Report: 3 Lead Plastic SOT89 Package (QTR: 10002 REV: 02)
- Package/Assembly Qualification Test Report: Plastic Encapsulated 4-LEAD MICRO-P (QTR: 05007 REV: 01)
- Semiconductor Qualification Test Report: SiGe HBT-A (QTR: 2013-00227)

DESIGN RESOURCES

- HMC481ST89 Material Declaration
- PCN-PDN Information
- Quality And Reliability
- Symbols and Footprints

DISCUSSIONS

View all HMC481ST89 EngineerZone Discussions.

SAMPLE AND BUY

Visit the product page to see pricing options.

TECHNICAL SUPPORT

Submit a technical question or find your regional support number.

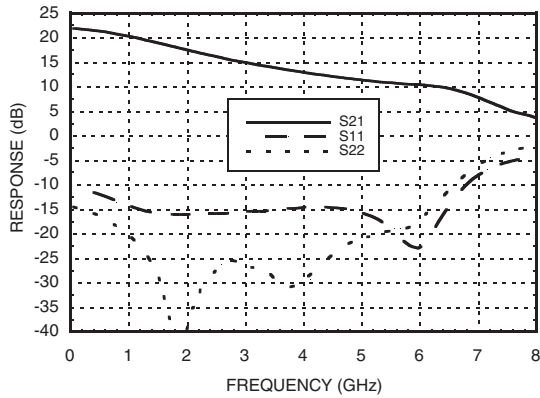
DOCUMENT FEEDBACK

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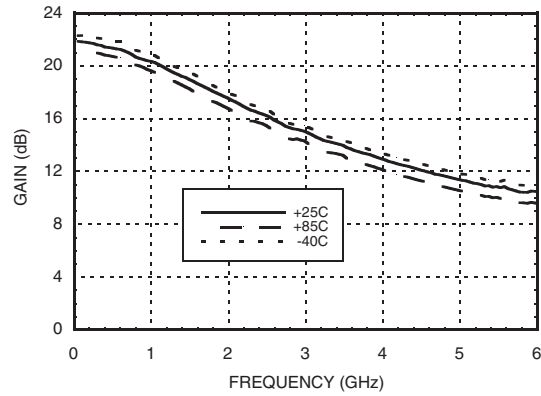


**SiGe HBT GAIN BLOCK
MMIC AMPLIFIER, DC - 5 GHz**

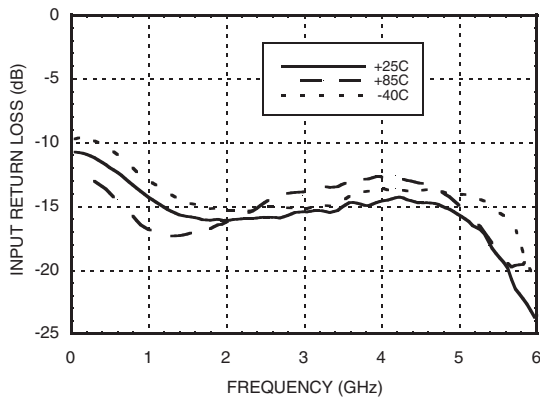
Broadband Gain & Return Loss



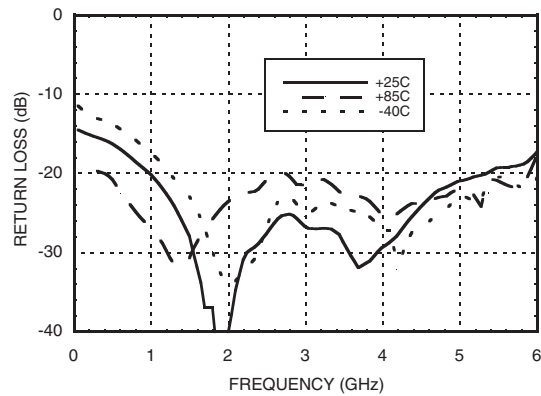
Gain vs. Temperature



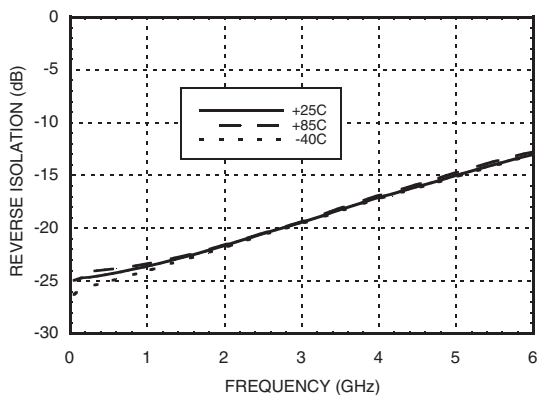
Input Return Loss vs. Temperature



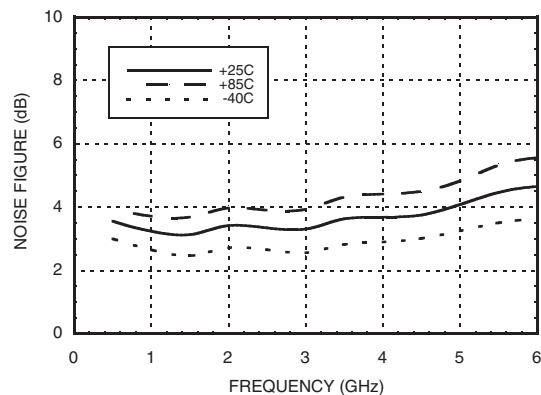
Output Return Loss vs. Temperature



Reverse Isolation vs. Temperature



Noise Figure vs. Temperature



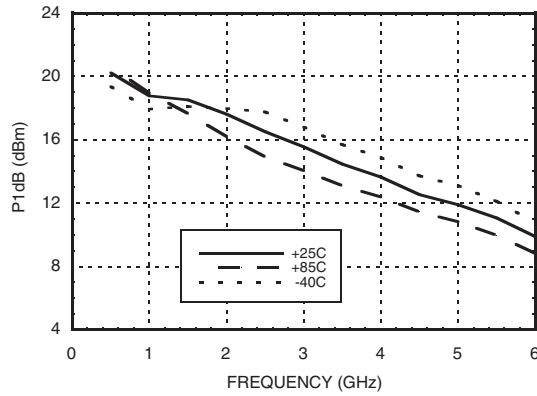
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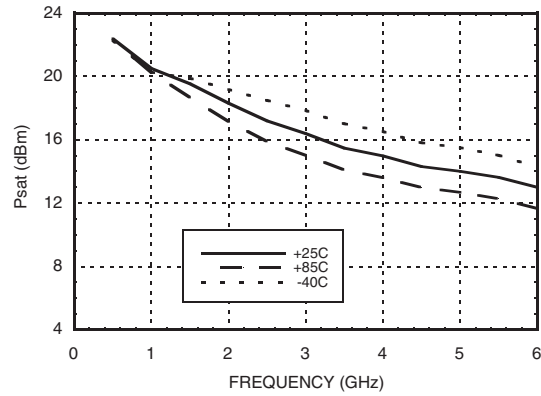


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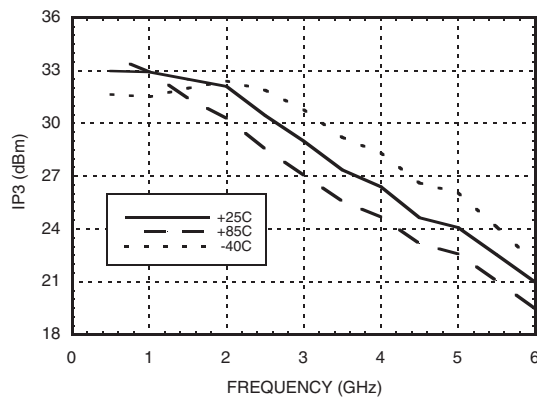
P1dB vs. Temperature



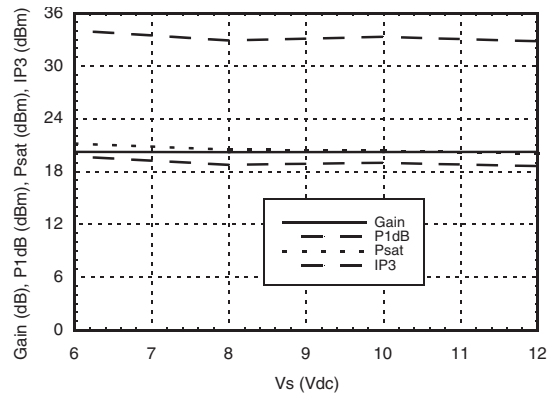
Psat vs. Temperature



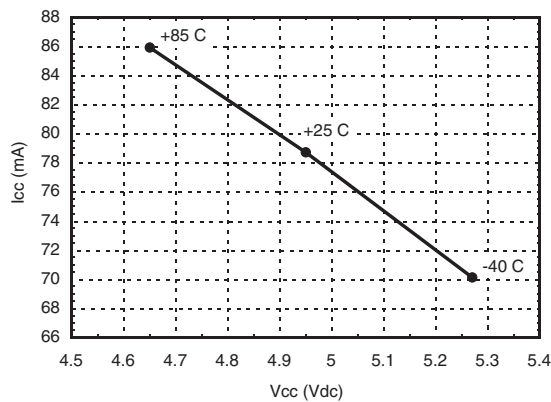
Output IP3 vs. Temperature



Gain, Power & OIP3 vs. Supply Voltage for Constant Icc= 79 mA @ 850 MHz



Vcc vs. Icc Over Temperature for Fixed Vs= 8V, RBIAS= 39 Ohms



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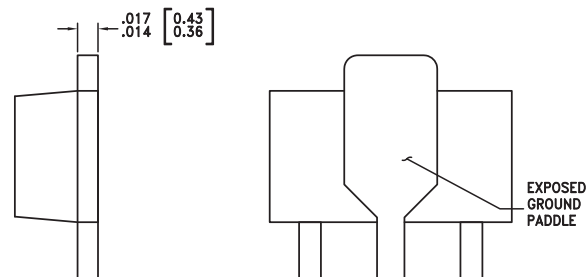
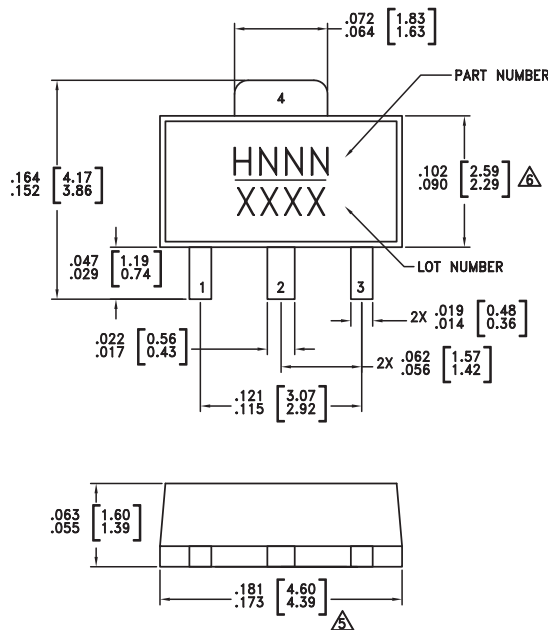
Absolute Maximum Ratings

| | |
|---|----------------|
| Collector Bias Voltage (Vcc) | +6.0 Vdc |
| RF Input Power (RFIN)(Vcc = +5 Vdc) | +10 dBm |
| Junction Temperature | 150 °C |
| Continuous P _{diss} (T = 85 °C) (derate 16.3 mW/°C above 85 °C) | 1.06 W |
| Thermal Resistance (junction to lead) | 61.4 °C/W |
| Storage Temperature | -65 to +150 °C |
| Operating Temperature | -40 to +85 °C |
| ESD Sensitivity (HBM) | Class 1A |



ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

Outline Drawing



NOTES:

- PACKAGE BODY MATERIAL:
MOLDING COMPOUND MP-180S OR EQUIVALENT.
- LEAD MATERIAL: Cu w/ Ag SPOT PLATING.
- LEAD PLATING: 100% MATTE TIN.
- DIMENSIONS ARE IN INCHES [MILLIMETERS]
- △ DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.15mm PER SIDE.
- △ DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.25mm PER SIDE.
- ALL GROUND LEADS MUST BE SOLDERED TO PCB RF GROUND.

Package Information

| Part Number | Package Body Material | Lead Finish | MSL Rating | Package Marking ^[3] |
|-------------|--|---------------|---------------------|--------------------------------|
| HMC481ST89 | Low Stress Injection Molded Plastic | Sn/Pb Solder | MSL1 ^[1] | H481 XXXX |
| HMC481ST89E | RoHS-compliant Low Stress Injection Molded Plastic | 100% matte Sn | MSL1 ^[2] | H481 XXXX |

[1] Max peak reflow temperature of 235 °C

[2] Max peak reflow temperature of 260 °C

[3] 4-Digit lot number XXXX

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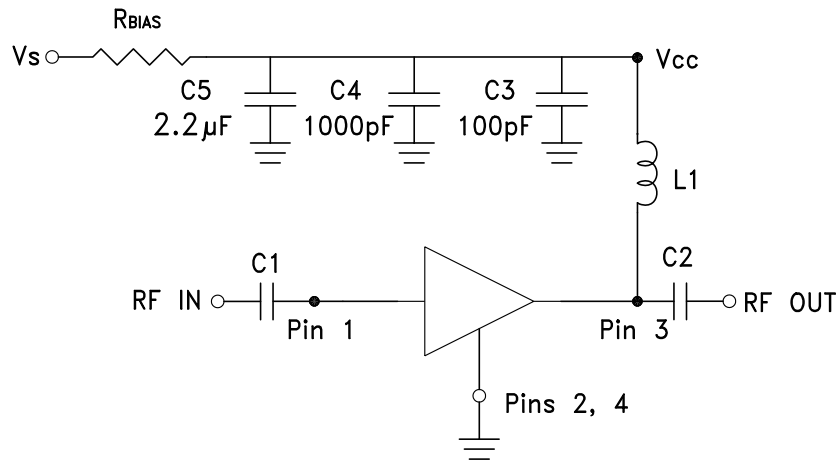


SiGe HBT GAIN BLOCK MMIC AMPLIFIER, DC - 5 GHz

Pin Descriptions

| Pin Number | Function | Description | Interface Schematic |
|------------|----------|---|---------------------|
| 1 | RFIN | This pin is DC coupled. An off chip DC blocking capacitor is required. | |
| 3 | RFOUT | RF output and DC Bias (Vcc) for the output stage. | |
| 2, 4 | GND | These pins and package bottom must be connected to RF/DC ground. | |

Application Circuit



Recommended Bias Resistor Values for $I_{cc} = 79 \text{ mA}$, $R_{bias} = (V_s - V_{cc}) / I_{cc}$

| Supply Voltage (Vs) | 6V | 8V | 10V | 12V |
|---------------------|-------------|-------------|-------------|-------------|
| RBIAS VALUE | 11 Ω | 39 Ω | 62 Ω | 91 Ω |
| RBIAS POWER RATING | 1/8 W | 1/4 W | 1/2 W | 1 W |

Note:

- External blocking capacitors are required on RFIN and RFOUT.
- RBIAS provides DC bias stability over temperature.

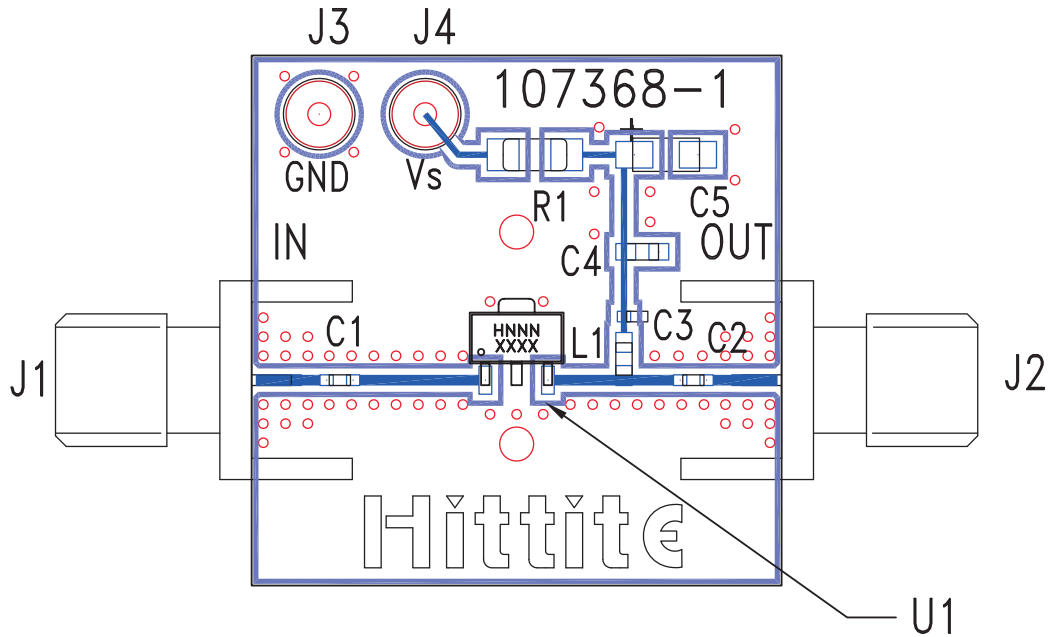
Recommended Component Values for Key Application Frequencies

| Component | Frequency (MHz) | | | | | | |
|-----------|--------------------|--------|--------|--------|--------|--------|--------|
| | 50 | 900 | 1900 | 2200 | 2400 | 3500 | 5000 |
| L1 | 270 nH | 56 nH | 18 nH | 18 nH | 15 nH | 8.2 nH | 6.8 nH |
| C1, C2 | 0.01 μF | 100 pF | 100 pF | 100 pF | 100 pF | 100 pF | 100 pF |



**SiGe HBT GAIN BLOCK
MMIC AMPLIFIER, DC - 5 GHz**

Evaluation PCB



List of Materials for Evaluation PCB 108324 [1]

| Item | Description |
|---------|------------------------------|
| J1 - J2 | PCB Mount SMA Connector |
| J3 - J4 | DC Pin |
| C1, C2 | Capacitor, 0402 Pkg. |
| C3 | 100 pF Capacitor, 0402 Pkg. |
| C4 | 1000 pF Capacitor, 0603 Pkg. |
| C5 | 2.2 μF Capacitor, Tantalum |
| R1 | Resistor, 1210 Pkg. |
| L1 | Inductor, 0603 Pkg. |
| U1 | HMC481ST89 / HMC481ST89E |
| PCB [2] | 107368 Evaluation PCB |

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the final application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and package bottom should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.